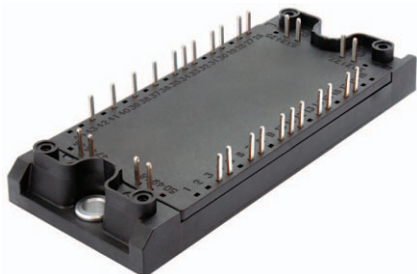


IGBT Fourpack Module, 75 A


ECONO2 4PACK

PRODUCT SUMMARY

V_{CES}	1200 V
I_C at $T_C = 67\text{ }^{\circ}\text{C}$	75 A
$V_{CE(on)}$ (typical)	3.4 V
Speed	8 kHz to 30 kHz
Package	ECONO2
Circuit	4 PACK

FEATURES

- Square RBSOA
- HEXFRED® low Q_{rr} , low switching energy
- Positive $V_{CE(on)}$ temperature coefficient
- Copper baseplate
- Low stray inductance design
- Designed and qualified for industrial market
- UL approved file E78996 
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT

BENEFITS

- Benchmark efficiency for SMPS appreciation in particular HF welding
- Rugged transient performance
- Low EMI, requires less snubbing
- Direct mounting to heatsink space saving
- PCB solderable terminals
- Low junction to case thermal resistance

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter voltage	V_{CES}		1200	V
Continuous collector current	I_C	$T_C = 25\text{ }^{\circ}\text{C}$	100	A
		$T_C = 80\text{ }^{\circ}\text{C}$	67	
Pulsed collector current See fig. C.T.5	I_{CM}		200	
Clamped inductive load current	I_{LM}		200	
Diode continuous forward current	I_F	$T_C = 25\text{ }^{\circ}\text{C}$	40	
		$T_C = 80\text{ }^{\circ}\text{C}$	25	
Diode maximum forward current	I_{FM}		150	
Gate to emitter voltage	V_{GE}		± 20	V
Maximum power dissipation (IGBT)	P_D	$T_C = 25\text{ }^{\circ}\text{C}$	480	W
		$T_C = 80\text{ }^{\circ}\text{C}$	270	
Maximum operating junction temperature	T_J		150	$^{\circ}\text{C}$
Storage temperature range	T_{Stg}		-40 to +125	
Isolation voltage	V_{ISOL}		AC 2500 (min)	V



ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	V _{BR(CES)}	V _{GE} = 0 V, I _C = 500 μA	1200	-	-	V
Collector to emitter voltage	V _{CE(ON)}	I _C = 75 A, V _{GE} = 15 V	-	3.4	4.0	
		I _C = 100 A, V _{GE} = 15 V	-	3.8	4.5	
		I _C = 75 A, V _{GE} = 15 V, T _J = 125 °C	-	4.0	4.5	
		I _C = 100 A, V _{GE} = 15 V, T _J = 125 °C	-	4.53	5.1	
Gate threshold voltage	V _{GE(th)}	V _{CE} = V _{GE} , I _C = 250 μA	4.0	5.0	6.0	mV/°C
Threshold voltage temperature coefficient	ΔV _{GE(th)} /ΔT _J	V _{CE} = V _{GE} , I _C = 1 mA (25 °C to 125 °C)	-	-11	-	
Zero gate voltage collector current	I _{CES}	V _{GE} = 0 V, V _{CE} = 1200 V	-	7	250	μA
		V _{GE} = 0 V, V _{CE} = 1200 V, T _J = 125 °C	-	580	2000	
Diode forward voltage drop	V _{FM}	I _F = 75 A	-	3.9	5.0	V
		I _F = 100 A	-	4.43	5.8	
		I _F = 75 A, T _J = 125 °C	-	4.37	5.4	
		I _F = 100 A, T _J = 125 °C	-	5.02	6.4	
Gate to emitter leakage current	I _{GES}	V _{GE} = ± 20 V	-	-	± 200	nA

SWITCHING CHARACTERISTICS (T _J = 25 °C unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Total gate charge (turn-on)	Q _G	I _C = 500 A V _{CC} = 600 V V _{GE} = 15 V	-	630	-	nC
Gate to emitter charge (turn-on)	Q _{GE}		-	65	-	
Gate to collector charge (turn-on)	Q _{GC}		-	250	-	
Turn-on switching loss	E _{on}	I _C = 50 A, V _{CC} = 600 V V _{GE} = 15 V, R _G = 4.7 Ω, L = 500 μH T _J = 25 °C ⁽¹⁾	-	1.51	-	mJ
Turn-off switching loss	E _{off}		-	2.41	-	
Total switching loss	E _{tot}		-	3.92	-	
Turn-on switching loss	E _{on}	I _C = 50 A, V _{CC} = 600 V V _{GE} = 15 V, R _G = 4.7 Ω, L = 500 μH T _J = 125 °C ⁽¹⁾	-	2.25	-	mJ
Turn-off switching loss	E _{off}		-	3.35	-	
Total switching loss	E _{tot}		-	7.60	-	
Turn-on delay time	t _{d(on)}	I _C = 50 A, V _{CC} = 600 V V _{GE} = 15 V, R _G = 4.7 Ω, L = 500 μH T _J = 125 °C	-	169	-	ns
Rise time	t _r		-	71	-	
Turn-off delay time	t _{d(off)}		-	393	-	
Fall time	t _f		-	136	-	
Reverse bias safe operating area	RBSOA	T _J = 150 °C, I _C = 150 A R _G = 10 Ω, V _{GE} = 15 V to 0 V	Fullsquare			
Short circuit safe operating area	SCSOA	T _J = 150 °C V _{CC} = 900 V, V _P = 1200 V R _G = 10 Ω, V _{GE} = 15 V to 0 V	10	-	-	μs
Diode peak reverse recovery current	I _{rr}	T _J = 25 °C	-	1.45	2.5	A
		T _J = 125 °C	-	2.35	4.0	
Diode reverse recovery time	t _{rr}	T _J = 25 °C	-	0.401	0.5	μs
		T _J = 125 °C	-	0.655	0.8	
Total reverse recovery charge	Q _{rr}	T _J = 25 °C	-	0.181	0.4	μC
		T _J = 125 °C	-	0.54	1.5	

Note

⁽¹⁾ Energy losses include "tail" and diode reverse recovery



THERMAL AND MECHANICAL SPECIFICATIONS

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS
Junction to case IGBT	R_{thJC} (IGBT)	-	-	0.26	°C/W
Junction to case DIODE	R_{thJC} (DIODE)	-	-	1.00	
Case to sink, flat, greased surface	R_{thCS} (MODULE)	-	0.05	-	
Mounting torque (M5)		2.7	-	3.3	Nm
Weight		-	170	-	g

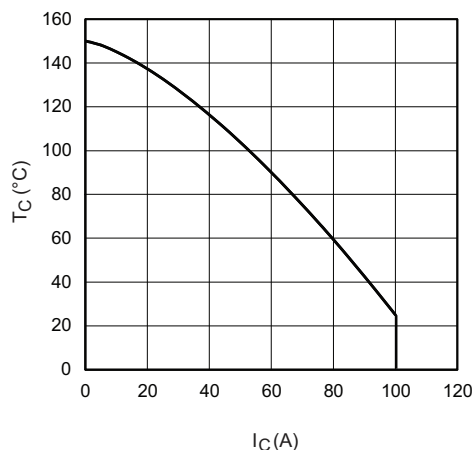


Fig. 1 - Maximum DC Collector Current vs. Case Temperature

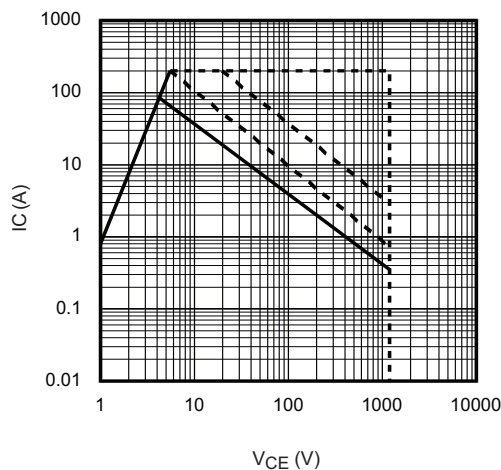


Fig. 3 - Forward SOA
 $T_C = 25^\circ\text{C}$; $T_J \leq 150^\circ\text{C}$

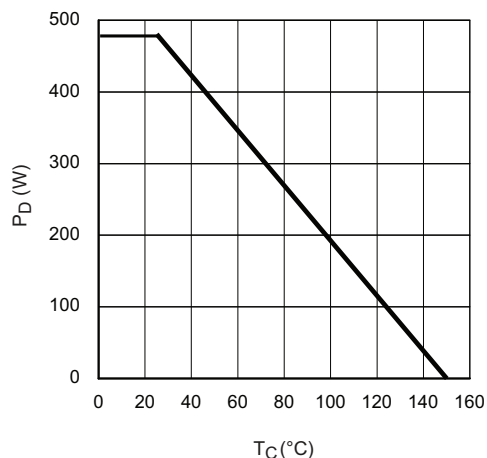


Fig. 2 - Power Dissipation vs. Case Temperature

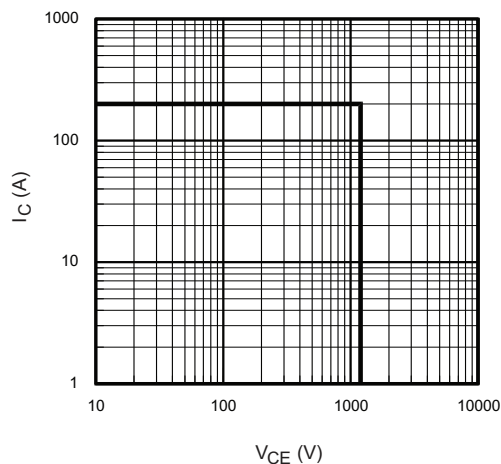


Fig. 4 - Reverse Bias SOA
 $T_J = 150^\circ\text{C}$; $V_{GE} = 15\text{ V}$

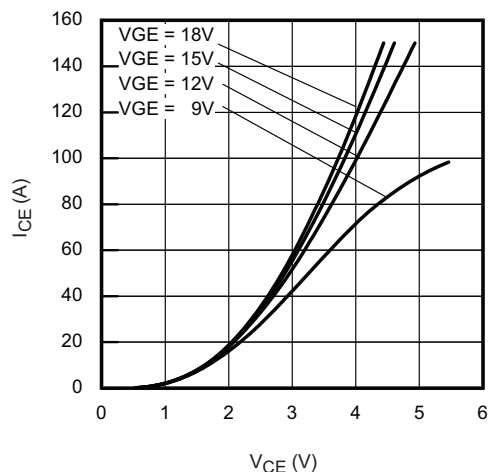


Fig. 5 - Typical IGBT Output Characteristics
 $T_J = 25^\circ\text{C}$; $t_p = 500\ \mu\text{s}$

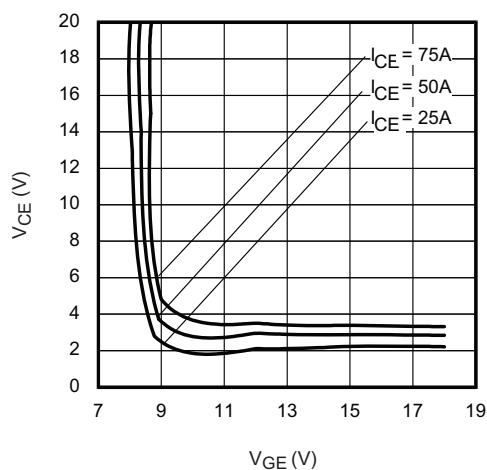


Fig. 8 - Typical V_{CE} vs. V_{GE}
 $T_J = 25^\circ\text{C}$

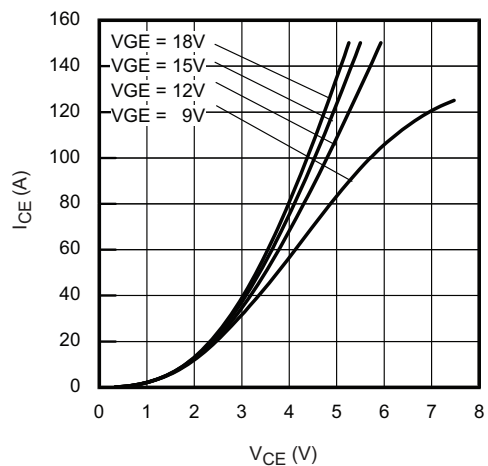


Fig. 6 - Typical IGBT Output Characteristics
 $T_J = 125^\circ\text{C}$; $t_p = 500\ \mu\text{s}$

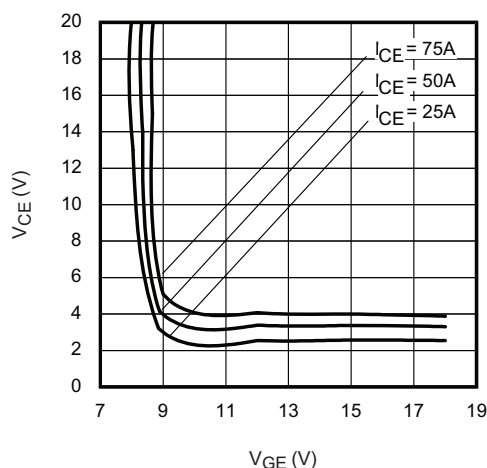


Fig. 9 - Typical V_{CE} vs. V_{GE}
 $T_J = 125^\circ\text{C}$

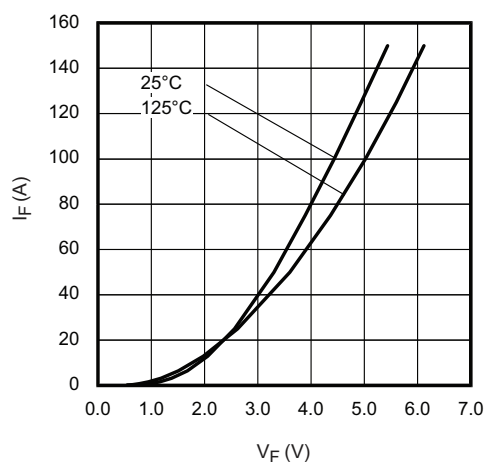


Fig. 7 - Typical Diode Forward Characteristics
 $t_p = 500\ \mu\text{s}$

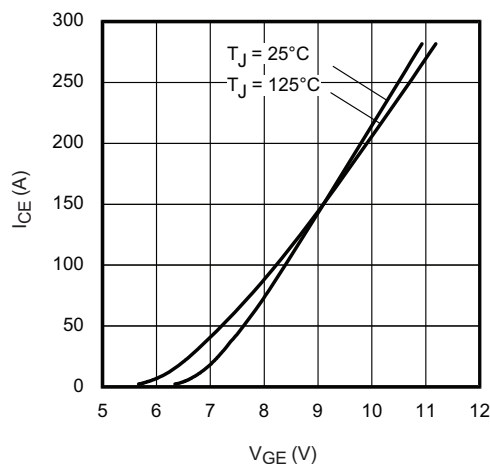


Fig. 10 - Typical Transfer Characteristics
 $V_{CE} = 20\ \text{V}$; $t_p = 500\ \mu\text{s}$

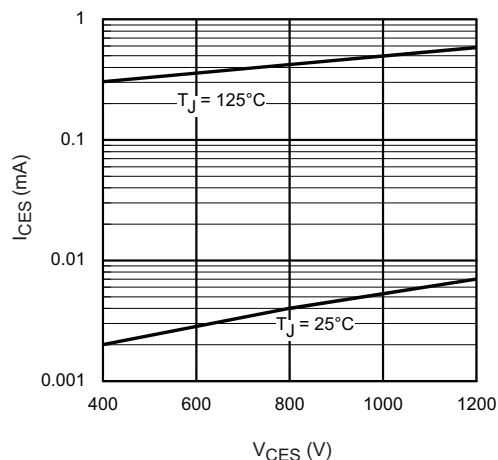


Fig. 11 - Typical Zero Gate Voltage Collector Current

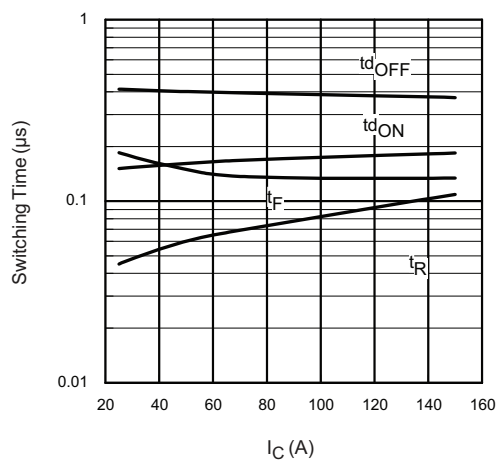
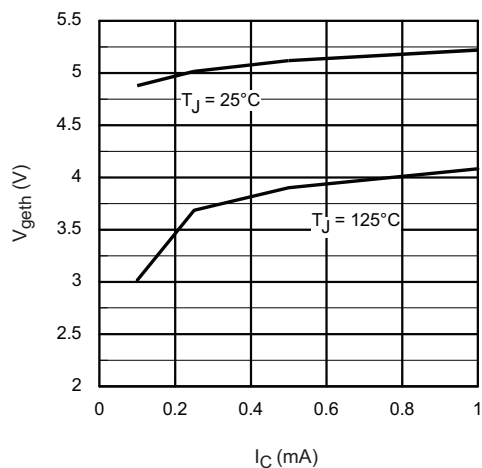
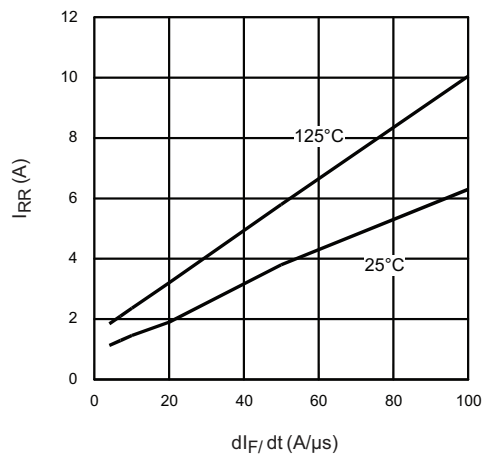
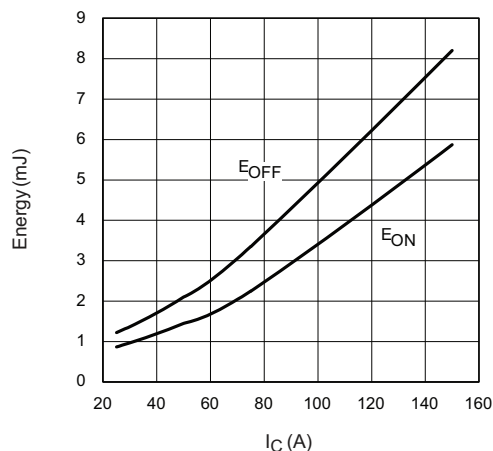
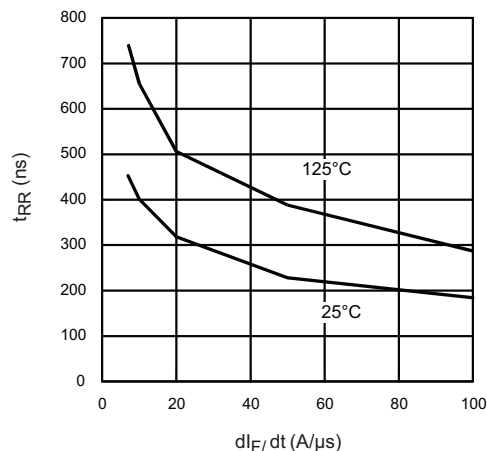

Fig. 14 - Typical Switching Time vs. I_C
 $T_J = 125^\circ\text{C}$; $L = 200\ \mu\text{H}$; $V_{CE} = 600\ \text{V}$; $R_G = 5\ \Omega$; $V_{GE} = 15\ \text{V}$


Fig. 12 - Typical Threshold Voltage


Fig. 15 - Typical Diode I_{REC} vs. dI_F/dt
 $V_{CC} = 600\ \text{V}$; $I_F = 50\ \text{A}$

Fig. 13 - Typical Energy Loss vs. I_C
 $T_J = 125^\circ\text{C}$; $L = 200\ \mu\text{H}$; $V_{CE} = 600\ \text{V}$; $R_G = 5\ \Omega$; $V_{GE} = 15\ \text{V}$

Fig. 16 - Typical Diode t_{rr} vs. dI_F/dt
 $V_{CC} = 600\ \text{V}$; $I_F = 50\ \text{A}$

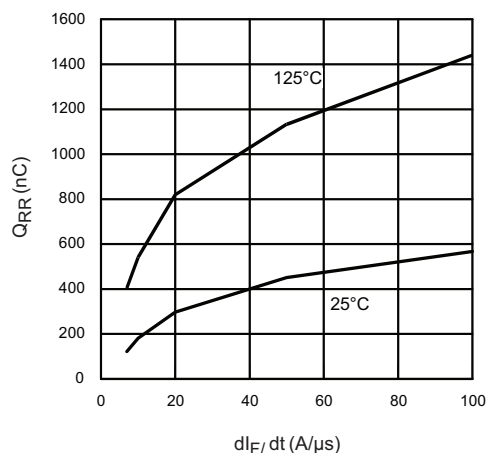


Fig. 17 - Typical Diode Q_{rr} vs. dI_F/dt
 $V_{CC} = 600\text{ V}$; $I_F = 50\text{ A}$

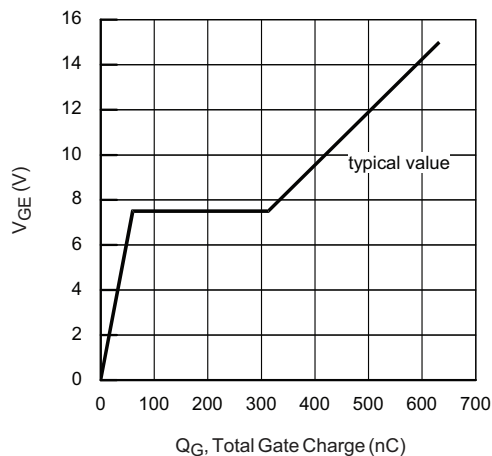


Fig. 18 - Typical Gate Charge vs. V_{GE}
 $I_{CE} = 5.0\text{ A}$; $L = 600\text{ μH}$

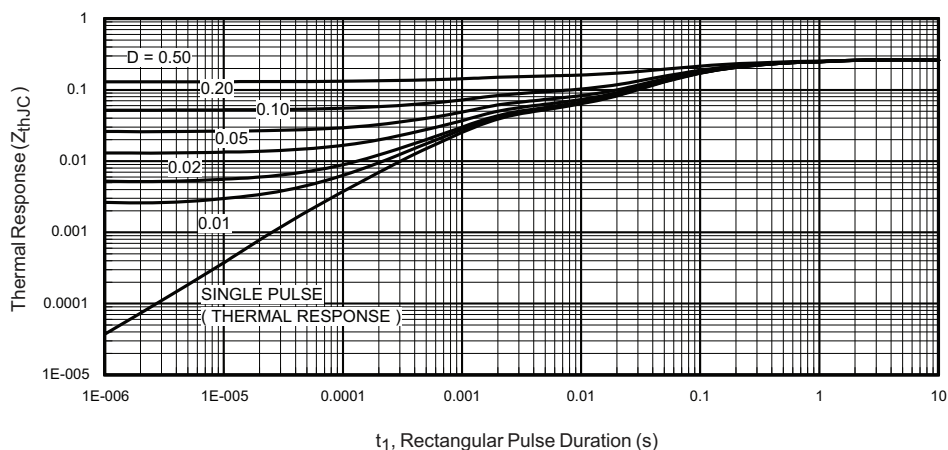


Fig. 19 - Maximum Transient Thermal Impedance, Junction to Case (IGBT)

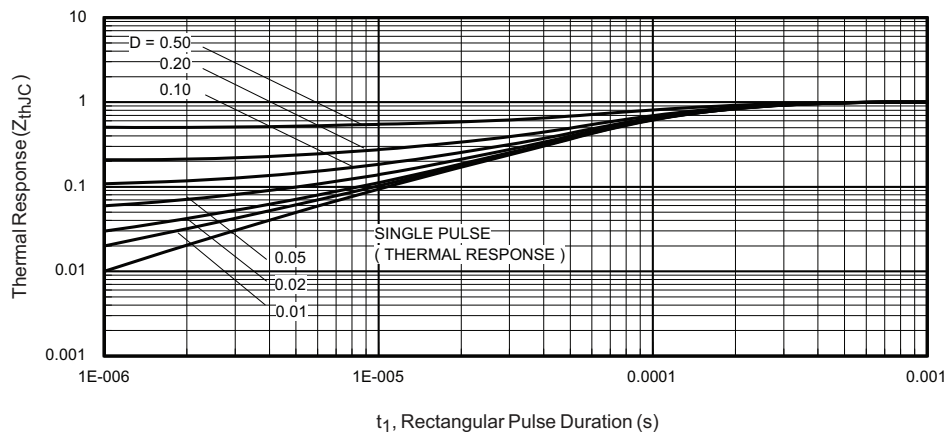


Fig. 20 - Maximum Transient Thermal Impedance, Junction to Case (DIODE)

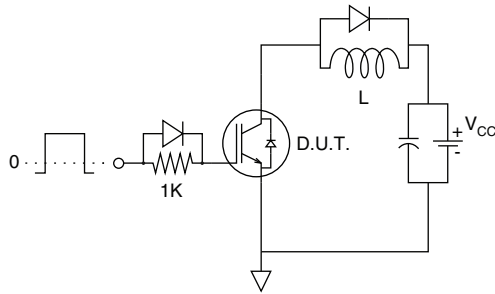


Fig. 21 - Gate Charge Circuit (Turn-Off)

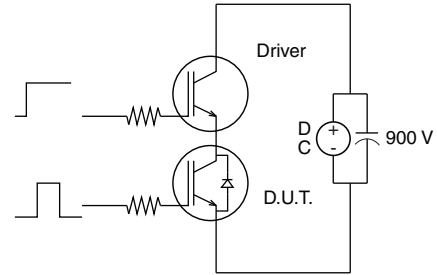


Fig. 23 - S.C. SOA Circuit

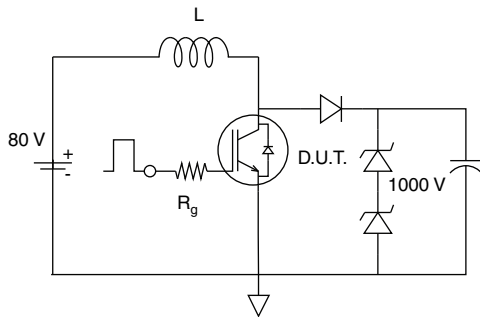


Fig. 22 - RBSOA Circuit

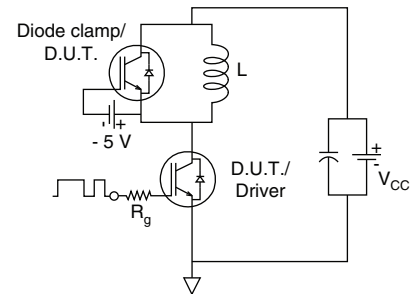


Fig. 24 - Switching Loss Circuit

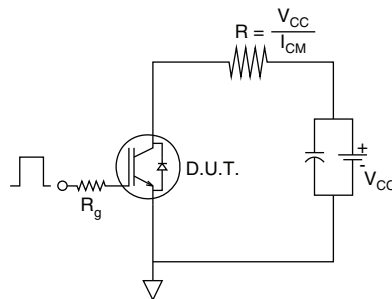
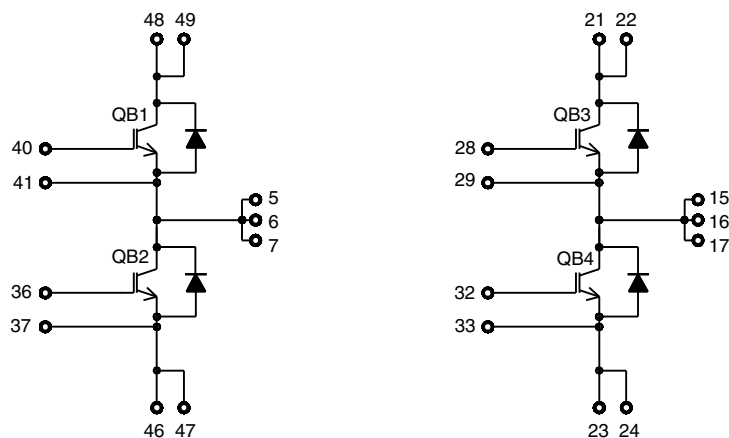


Fig. 25 - Resistive Load Circuit

ORDERING INFORMATION TABLE

Device code	VS-	G	B	75	Y	F	120	N
	1	2	3	4	5	6	7	8

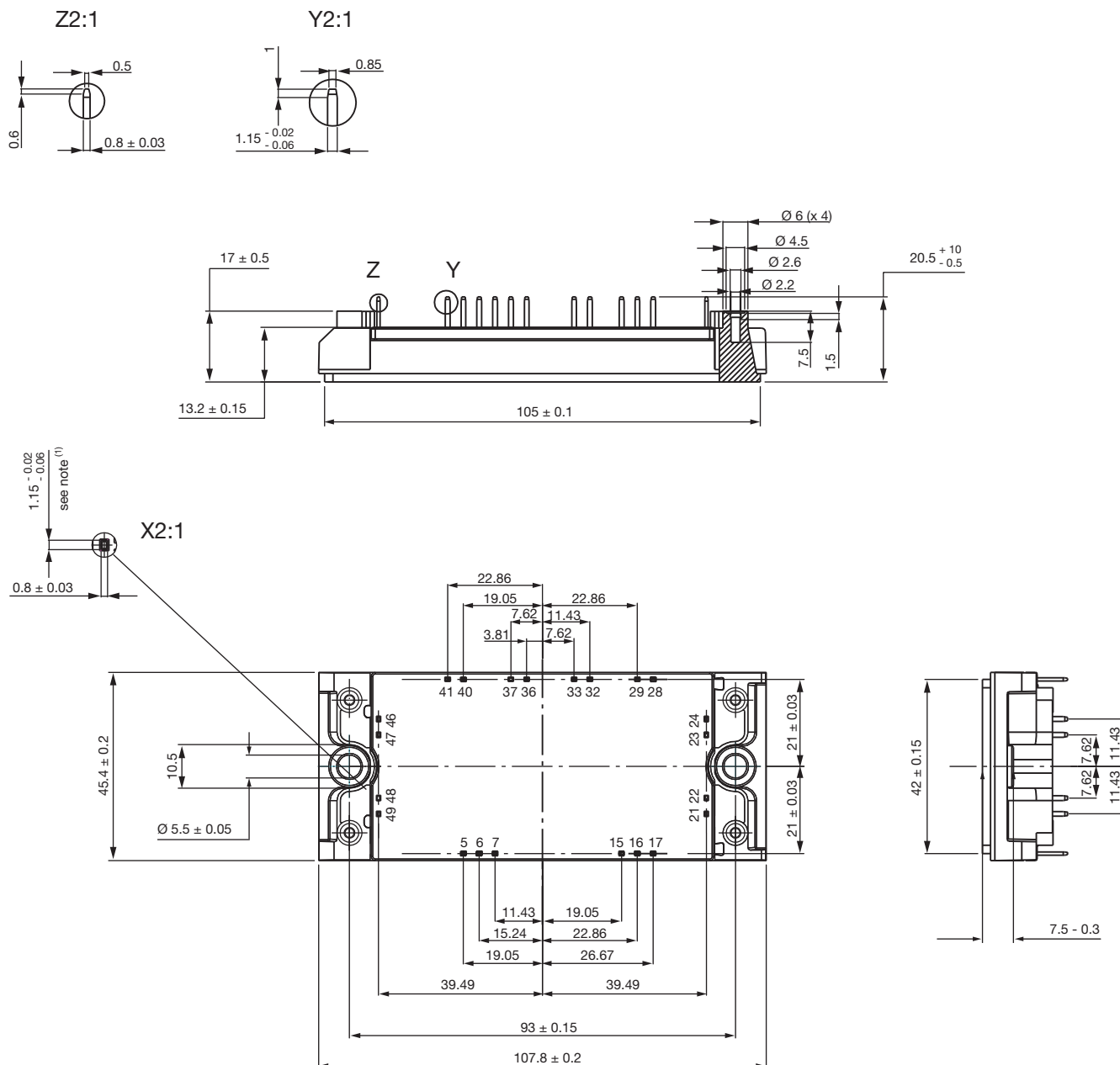
- | | | |
|---|---|--|
| 1 | - | Vishay Semiconductors product |
| 2 | - | Insulated gate bipolar transistor (IGBT) |
| 3 | - | B = IGBT Generation 5 NPT |
| 4 | - | Current rating (75 = 75 A) |
| 5 | - | Circuit configuration (Y = Fourpack) |
| 6 | - | Package indicator (F = ECONO2) |
| 7 | - | Voltage rating (120 = 1200 V) |
| 8 | - | Speed/type (N = Ultrafast with reduced diode, speed 8 kHz to 60 kHz) |

CIRCUIT CONFIGURATION

LINKS TO RELATED DOCUMENTS

Dimensions	www.vishay.com/doc?95539
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ECONO2 4PACK N Series

DIMENSIONS in millimeters





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